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## Contents

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<b>Preface</b> .....	ix
Nicolas POSSEME	
<b>Chapter 1. CMOS Devices Through the Years</b> .....	1
Maud VINET and Nicolas POSSEME	
1.1. Scaling law by Dennard .....	4
1.2. CMOS device improvement through the years .....	6
1.2.1. Mobility improvement .....	6
1.2.2. Leakage current reduction .....	8
1.2.3. Gate-last approach .....	11
1.2.4. New transistor generations .....	12
1.2.5. Patterning challenges for FinFET and FDSOI .....	15
1.3. Summary .....	17
1.4. What is coming next? .....	18
1.5. Bibliography .....	19
<b>Chapter 2. Plasma Etching in Microelectronics</b> .....	23
Maxime DARNON	
2.1. Overview of plasmas and plasma etch tools .....	23
2.1.1. Overview of plasmas .....	23
2.1.2. Typical plasma etch tools in the semiconductor industry .....	28
2.2. Plasma surface interactions during plasma etching .....	35
2.2.1. Purely spontaneous etching (downstream plasmas) .....	36
2.2.2. Purely physical etching (ion beam etching) .....	37
2.2.3. Reactive IBE (RIBE) .....	39

2.2.4. Chemically assisted IBE (CAIBE) . . . . .	40
2.2.5. Real plasma etching mechanisms . . . . .	41
2.2.6. Impact of plasma parameters on plasma etching . . . . .	43
2.2.7. Reactor walls and plasma etching . . . . .	44
2.2.8. Plasma changes due to etching . . . . .	45
2.3. Patterns transfer by plasma etching . . . . .	46
2.3.1. Pattern-related phenomena . . . . .	46
2.3.2. Pattern profile obtained by plasma etching . . . . .	52
2.4. Conclusion . . . . .	54
2.5. Bibliography . . . . .	55
<b>Chapter 3. Patterning Challenges in Microelectronics . . . . .</b>	<b>59</b>
Sébastien BARNOLA, Nicolas POSSEME, Stefan LANDIS and Maxime DARNON	
3.1. Optical immersion lithography . . . . .	59
3.1.1. Principle . . . . .	59
3.1.2. Immersion lithography challenges for plasma etching . . . . .	62
3.2. Next-generation lithography . . . . .	66
3.2.1. Multiple patterning techniques . . . . .	67
3.2.2. EUV lithography . . . . .	74
3.2.3. E-beam lithography . . . . .	77
3.2.4. Direct self-assembly . . . . .	79
3.2.5. Nanoimprint lithography (NIL) . . . . .	87
3.3. Conclusion . . . . .	90
3.4. Bibliography . . . . .	91
<b>Chapter 4. Plasma Etch Challenges for Gate Patterning . . . . .</b>	<b>95</b>
Maxime DARNON and Nicolas POSSEME	
4.1. pSi gate etching . . . . .	97
4.1.1. Etching processes in HBr/Cl <sub>2</sub> /O <sub>2</sub> . . . . .	97
4.1.2. Etching in fluorine-based plasmas . . . . .	99
4.1.3. Comparison between the two options . . . . .	100
4.2. Metal gate etching . . . . .	102
4.2.1. Generalities on metal etching requirements . . . . .	102
4.2.2. TiN etching . . . . .	102
4.2.3. Other metals . . . . .	104

4.3. Stopping on the gate oxide . . . . .	104
4.3.1. Foot/notch formation . . . . .	104
4.3.2. Selectivity issues with thin SiO <sub>2</sub> and silicon recess . . . . .	105
4.3.3. Selectivity/residues with high-k dielectrics . . . . .	108
4.4. High-k dielectric etching . . . . .	109
4.5. Line width roughness transfer during gate patterning . . . . .	110
4.6. Chamber wall consideration after gate patterning . . . . .	111
4.7. Summary . . . . .	113
4.8. Bibliography . . . . .	113
<b>List of Acronyms</b> . . . . .	119
<b>List of Authors</b> . . . . .	123
<b>Index</b> . . . . .	125